

April 2008



# FJD5553 NPN Silicon Transistor

## **High Voltage Switch Mode Application**

- Fast Speed Switching
- Wide Safe Operating Area
- Suitable for Electronic Ballast Application



## Absolute Maximum Ratings \* T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
BV <sub>CBO</sub>	Collector-Base Voltage	1050	V	
BV <sub>CEO</sub>	Collector-Emitter Voltage	400	V	
BV <sub>EBO</sub>	Emitter-Base Voltage	14	V	
I <sub>C</sub>	Collector Current (DC)	3	A	
I <sub>CP</sub>	Collector Current (Pulse)	6	A	
Ι <sub>Β</sub>	Base Current (DC)	1	A	
I <sub>BP</sub>	Collector Current (Pulse)	2	A	
P <sub>C</sub>	Collector Dissipation	1.25	W	
TJ	Junction Temperature	150 °C		
T <sub>STG</sub>	Storage Junction Temperature Range	- 55 ~ 150	°C	

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### Thermal Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	100	°C/W

Device mounted on minimum pad size

## **Ordering Information**

Part Number	Marking	Package	Packing Method	Remarks
FJD5553TM	J5553	D-PAK	Tape & Reel	

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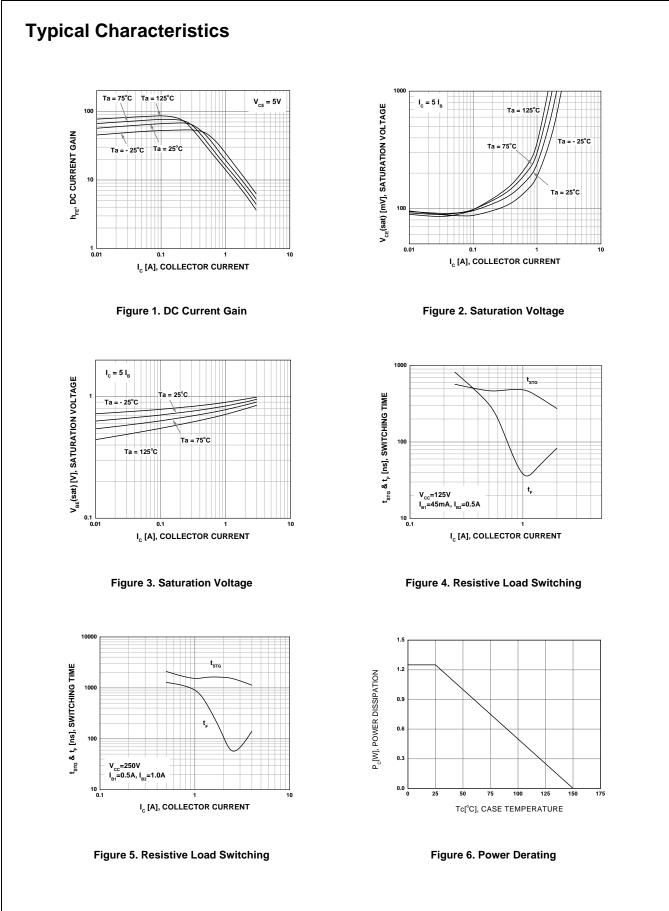
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Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =500μA, I <sub>E</sub> =0	1050			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =5mA, I <sub>B</sub> =0	400			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =500μA, I <sub>C</sub> =0	14			V
h <sub>FE</sub>	* DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	10			
		V <sub>CE</sub> =3V, I <sub>C</sub> =0.4A	30		60	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =1A, I <sub>B</sub> =0.2A		0.23	0.5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =1A, I <sub>B</sub> =0.2A			1.2	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, f=1MHz		45		pF
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> =125V, I <sub>C</sub> =0.5A			1.0	μS
t <sub>STG</sub>	Storage Time	I <sub>B1</sub> =45mA, I <sub>B2</sub> =0.5A R <sub>I</sub> =250Ω			1.2	μS
t <sub>F</sub>	Fall Time			0.3		μS
t <sub>ON</sub>	Turn On Time	$V_{CC}$ =250V, I <sub>C</sub> =2.5A I <sub>B1</sub> =0.5A, I <sub>B2</sub> =1.0A R <sub>L</sub> =100 $\Omega$			2.0	μS
t <sub>STG</sub>	Storage Time				2.5	μS
t <sub>F</sub>	Fall Time				0.3	μS
EAS	Avalanche Energy	L= 2mH	3.5			mJ

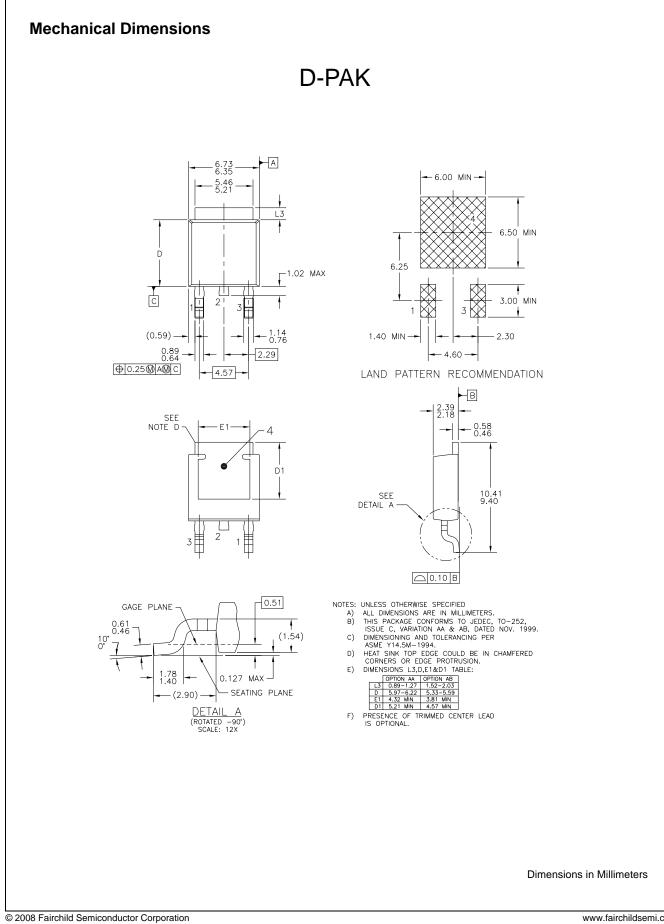
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